

1. General description

Planar passivated high commutation three quadrant triac in a SOT223 surface mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Applications

- General purpose motor controls
- Home appliances
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

3. Quick reference data

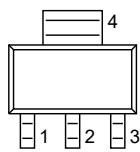
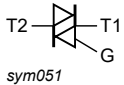
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 108\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(initial)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	11	A
		full sine wave; $T_{j(initial)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	10	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 9	-	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 9	-	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 9	-	-	35	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 11	-	-	20	mA
V_T	on-state voltage	$I_T = 2\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12	-	0.7	1.5	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ °C}$; (67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/ μ s

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
di_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 1\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	3	-	-	A/ms

4. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>SC-73 (SOT223)</p>	
2	T2	main terminal 2		
3	G	gate		
4	mb	mounting base; connected to main terminal 2		

5. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA204W-800C	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

6. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 108\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	11	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	10	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.5	A ² s
di_T/dt	rate of rise of on-state current	$I_G = 0.2\text{ A}$	-	100	A/ μ s
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	125	°C

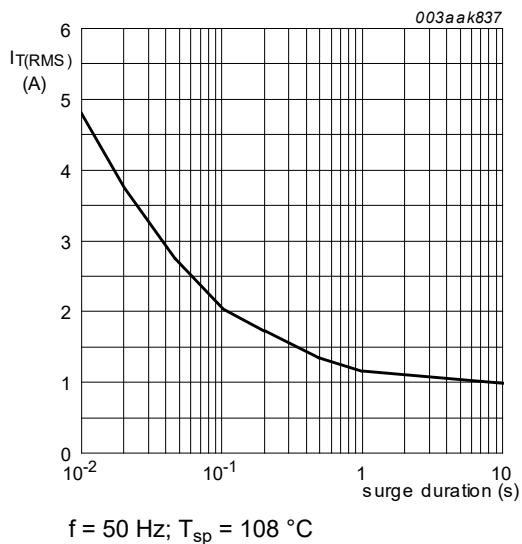


Fig. 1. RMS on-state current as a function of surge duration; maximum values

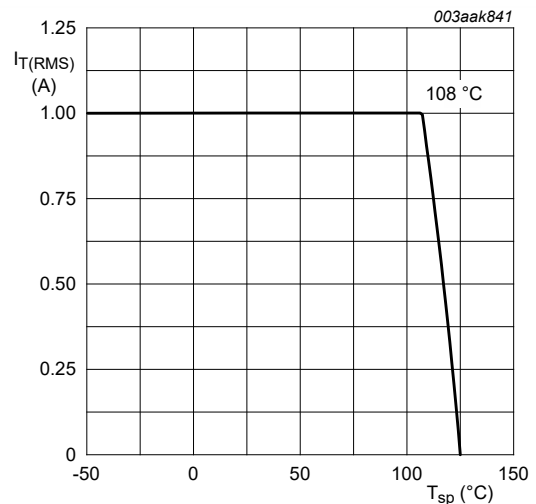


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

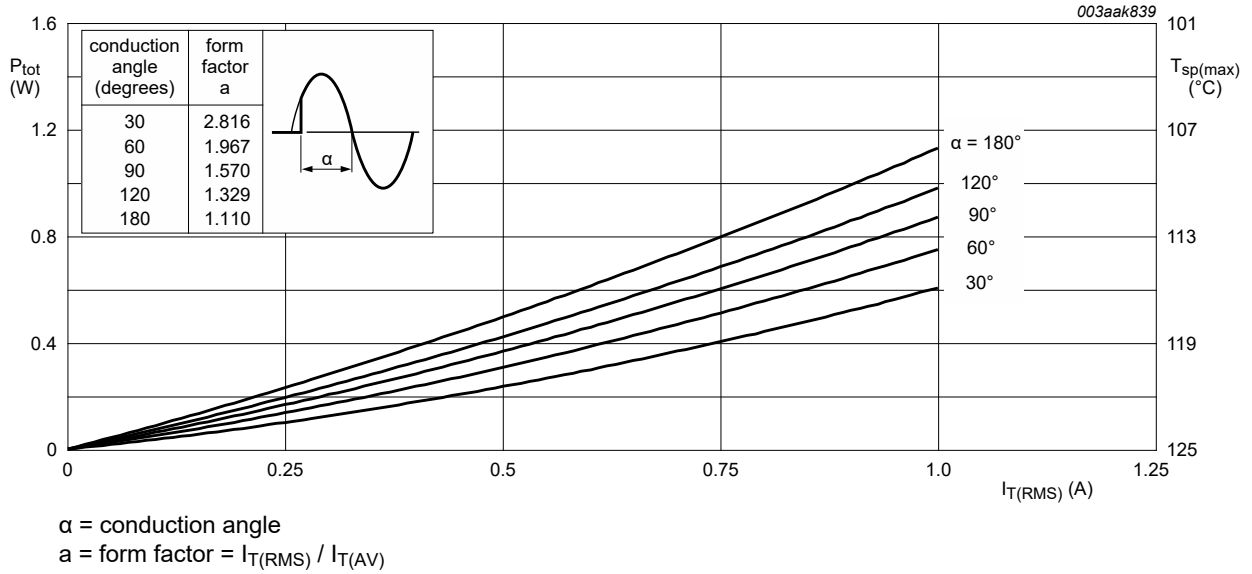


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

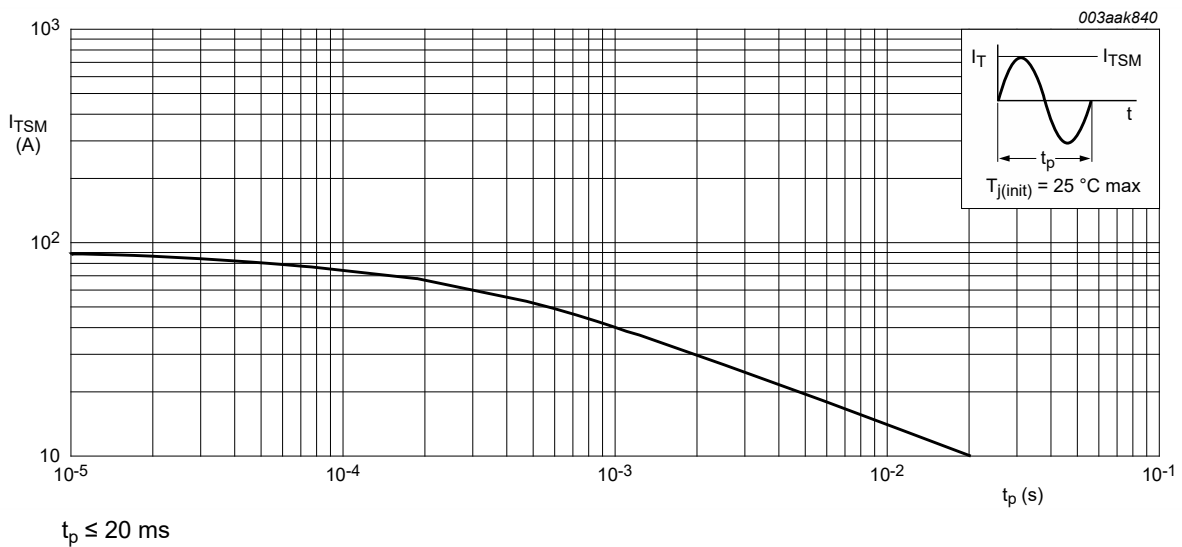
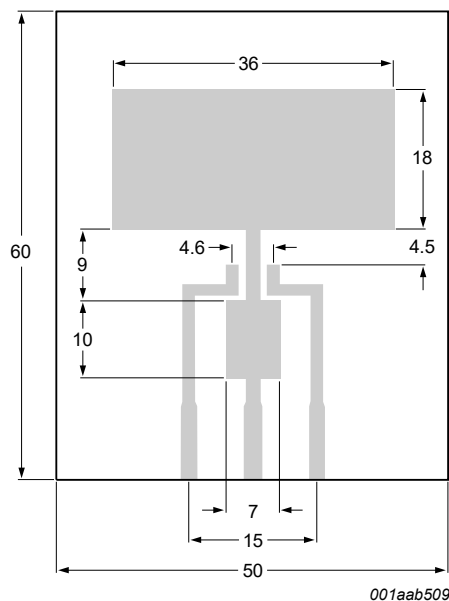
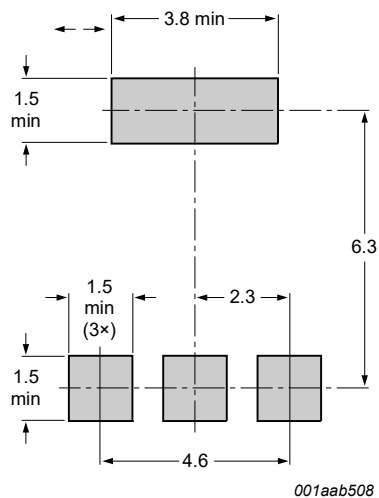


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values



All dimensions are in mm
Printed circuit board:
FR4 epoxy glass (1.6 mm thick), copper laminate
(35 um thick)

Fig. 7. Printed circuit board pad area: SOT223



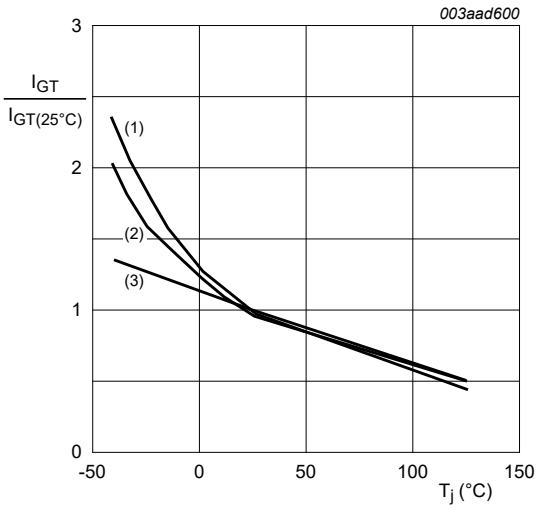
All dimensions are in mm

Fig. 8. Minimum footprint SOT223

8. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 9	-	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 9	-	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 9	-	-	35	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 10	-	-	20	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 10	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 10	-	-	20	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 11	-	-	20	mA
V _T	on-state voltage	I _T = 2 A; T _j = 25 °C; Fig. 12	-	0.7	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 13	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 13	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (67% of V _{DRM}); exponential waveform; gate open circuit	1000	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 1 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit	3	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

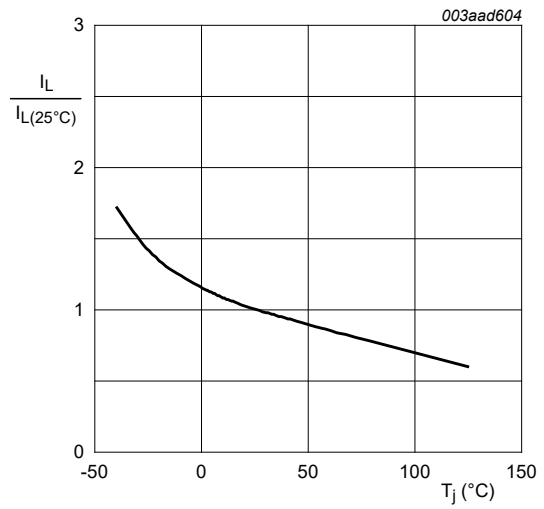


Fig. 10. Normalized latching current as a function of junction temperature

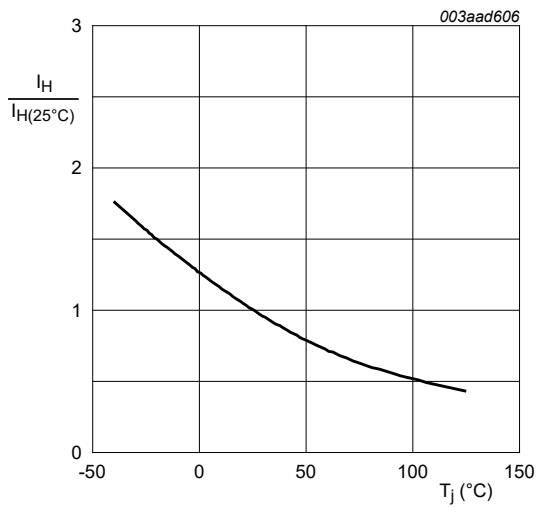
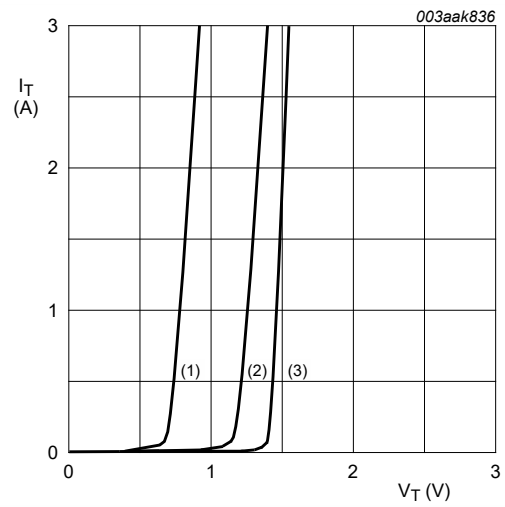


Fig. 11. Normalized holding current as a function of junction temperature



$V_o = 1.27 \text{ V}; R_s = 0.091 \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 12. On-state current as a function of on-state voltage

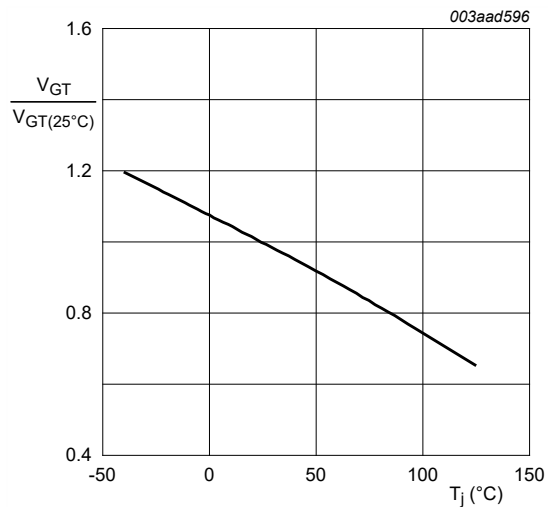
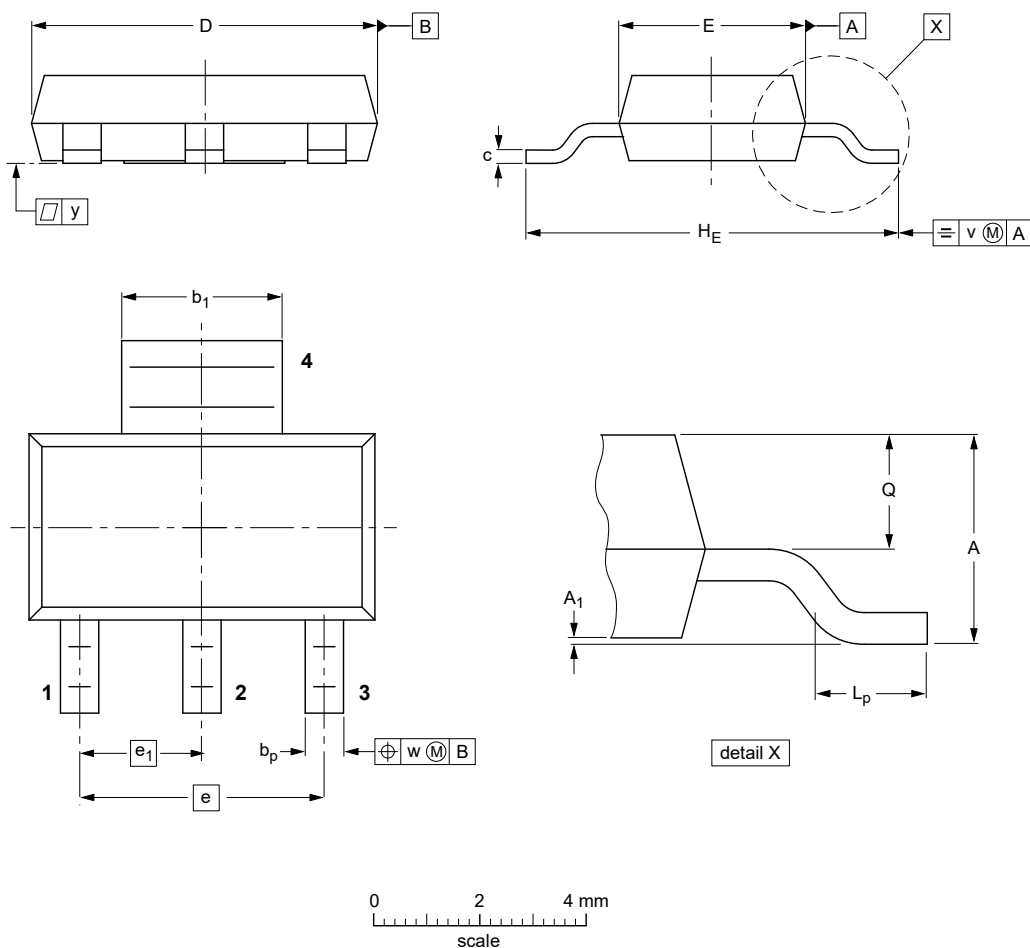


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

9. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.8	0.10	0.80	3.1	0.32	6.7	3.7	4.6	2.3	7.3	1.1	0.95	0.2	0.1	0.1
	1.5	0.01	0.60	2.9	0.22	6.3	3.3			6.7	0.7	0.85			

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